



2/2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application

Inventor: Tatau NISHINAGA Group Art Unit: 1765
Appln. No.: 09/511,912 Examiner: M. Anderson
Filed: February 23, 2000
For: A METHOD FOR FORMING A SINGLE CRYSTALLINE FILM

CERTIFICATION UNDER 37 CFR §1.97(e)(1)

Assistant Commissioner of Patents
Washington, DC 20231

Dear Sir:

In fulfillment of 37 CFR 1.97(c)(1) and 1.97(e)(1), it is hereby certified that each item of information contained in the attached Information Disclosure Statement was first cited in any communication (see the attached copy of a German Office Action dated June 21, 2004) from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

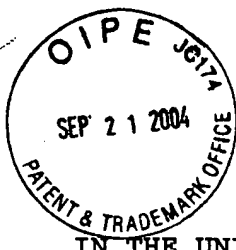
Respectfully submitted,

James E. Ledbetter
Registration No. 28,732

Date: September 21, 2004

JEL/spp

ATTORNEY DOCKET NO. JEL31015
STEVENS, DAVIS, MILLER & MOSHER, L.L.P.
1615 L STREET, NW, Suite 850
P.O. Box 34387
WASHINGTON, DC 20043-4387
TELEPHONE: (202) 785-0100
FACSIMILE: (202) 408-5200



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Inventor: Tatau NISHINAGA Group Art Unit: 1765
Appln. No.: 09/511,912 Examiner: M. Anderson
Filed: February 23, 2000
For: A METHOD FOR FORMING A SINGLE CRYSTALLINE FILM

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner of Patents
Washington, DC 20231

Dear Sir:

Pursuant to Rules 56 and 99, Applicants hereby call the attention of the Patent Office to the art listed on the attached Form PTO 1449. All of these references were cited in a German Office Action dated June 21, 2004 (English translation attached) except for US '473. US '473 corresponds to DE '186.

Applicants present this art so that the Patent Office may, in the first instance, determine any relevancy thereof to the presently claimed invention, see Beckman Instruments, Inc. v. Chemtronics, Inc., 439 F.2d 1369, 1380, 165 USPQ 355, 364 (5th Cir. 1970). Also see Patent Office Rules 104 and 106. Applicants respectfully request that this art be expressly considered during the prosecution of this application and made of record herein and appear among the "References Cited" on any patent to issue herefrom.

Respectfully submitted,

James E. Ledbetter
Registration No. 28,732

Date: September 21, 2004

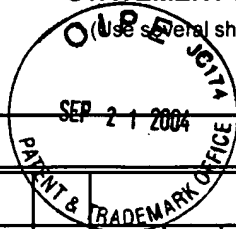
JEL/spp

ATTORNEY DOCKET NO. JEL31015
STEVENS, DAVIS, MILLER & MOSHER, L.L.P.
1615 L STREET, NW, Suite 850
WASHINGTON, DC 20043-4387
Telephone: (202) 785-0100
Facsimile: (202) 408-5200

FORM PTO-1449 U.S. Department of Commerce
(Rev. 4/92) Patent and Trademark Office

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)



ATTY. DOCKET NO.

JEL31015

SERIAL NO.

09/511,592

APPLICANT

Tatau NISHINAGA

FILING DATE

February 23, 2000

GROUP

1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6 3 9 9 4 7 3	06/2002	Fischer et al.			
	4 1 7 1 2 3 4	10/1979	Nagata et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO
6 1 2 7 1 8 1 7	12/1986	JP			Abstract
1 9 7 2 9 1 8 6	01/1999	DE			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

German Office Action dated June 21, 2004 with English translation.

H. GOSSNER, et al.; "Self-Organizing Growth of Nanometer Mesa Structures on Silicon (100) Substrates", Jpn. J. Appln. Phys. Vol. 33 (1994) pp. 2268-2271, Part 1, No. 4B, April 1994.

B-Y. TSAUR, et al.; "Low-dislocation-density GaAs epilayers grown on Ge-coated Si substrates by means of lateral epitaxial overgrowth", Appln. Phys. Lett. 41(4), 15 August 1982, pp. 347-349.

Y. MATSUNAGA, et al.; "Microchannel Epitaxy of GaAs ON Si(100) Substrates Using SiO₂ Shadow Masks", Electrochemical Society Proceedings Volume 97-21 (1997), pp. 184-188.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.